





LOW $V_{\text{CE(SAT)}}$ PNP SURFACE MOUNT TRANSISTOR

Features

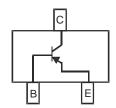
- **Epitaxial Planar Die Construction**
- Complementary NPN Type Available (DNLS160)
- Surface Mount Package Suited for Automated Assembly
- Lead Free/RoHS Compliant (Note 1)

"Green Device" (Note 2) Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-1	Α
Peak Pulse Collector Current	I _{CM}	-2	Α
Base Current (DC)	I _B	-300	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	300	mW
Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

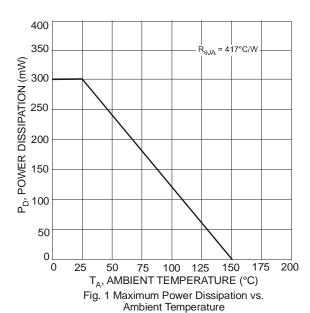
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Electrical Characteristics @T_A = 25°C unless otherwise specified

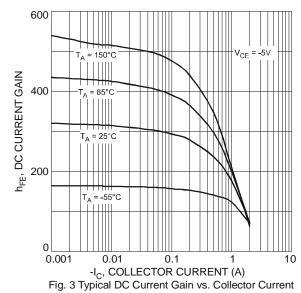
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 4)								
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80	_	_	V	$I_C = -100 \mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_		V	$I_C = -10 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5	_		V	$I_E = -100 \mu A, I_C = 0$		
Collector Cutoff Current	I _{CBO}		_	-100	nA	$V_{CB} = -60V, I_{E} = 0$		
Concetor Caton Carrent	ICBO			-50	μΑ	$V_{CB} = -60V$, $I_E = 0$, $T_A = 150$ °C		
Collector Cutoff Current	I _{CES}		_	-100	nA	$V_{CE} = -60V, V_{BE} = 0$		
Emitter Cutoff Current	I _{EBO}		_	-100	nA	$V_{EB} = -5V, I_C = 0$		
ON CHARACTERISTICS (Note 4)								
		200	325			$V_{CE} = -5V$, $I_C = -1mA$		
DC Current Gain	h _{FE}	150	250	_	V	$V_{CE} = -5V, I_{C} = -500mA$		
		100	180			$V_{CE} = -5V, I_{C} = -1A$		
		_	-90	-160		$I_C = -100 \text{mA}, I_B = -1 \text{mA}$		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	-90	-175	mV	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$		
			-160	-330		$I_C = -1A$, $I_B = -100mA$		
Collector-Emitter Saturation Resistance	R _{CE(SAT)}		160	330	mΩ	$I_C = -1A$, $I_B = -100mA$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-0.95	-1.1	V	$I_C = -1A$, $I_B = -50mA$		
Base-Emitter Turn On Voltage	V _{BE(ON)}		-0.82	-0.9	V	$V_{CE} = -5V, I_{C} = -1A$		
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	C _{obo}		10	15	pF	V _{CB} = -10V, f = 1.0MHz		
Current Gain-Bandwidth Product	f _T	150	220		MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$		

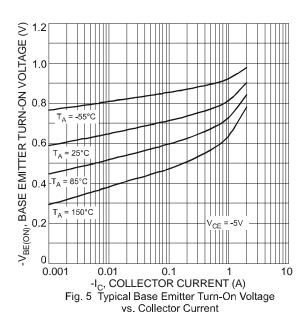
Notes: 4. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.

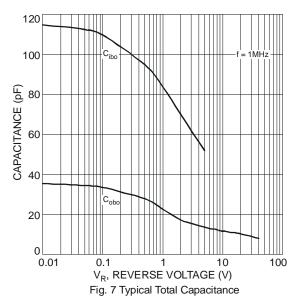


1.5 $I_B = -10mA$ -I°. COLLECTOR CURRENT (A) 0.0 0.0 0.0 0.0 $I_B = -6 \text{mA}$ $I_B = -4 \text{mA}$ $I_B = -2mA$ 0 1 2 3 4 -V_{CE}, COLLECTOR-EMITTER VOLTAGE (V) 5 Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage









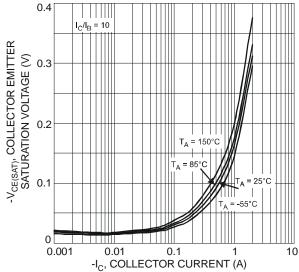


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

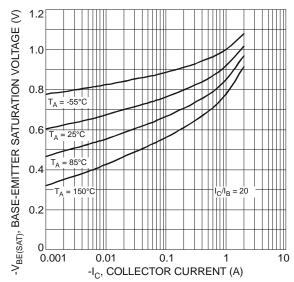
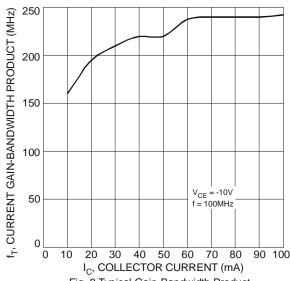


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



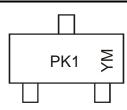


Ordering Information (Note 5)

Device	Packaging	Shipping
DPLS160-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



PK1 = Product Type Marking Code YM = Date Code Marking

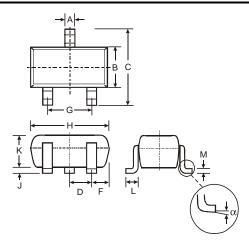
Y = Year ex: U = 2007

M = Month ex: 9 = September

Date Code Key

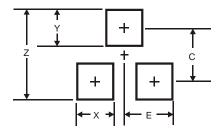
Year	2008		2009	2010	١	2011	2012	!	2013	2014	ı	2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89	1.03			
F	0.45	0.60			
G	1.78	2.05			
Н	2.80	3.00			
J	0.013	0.10			
K	0.903	1.10			
L	0.45	0.61			
M	0.085	0.180			
α	0°	8°			
All Di	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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